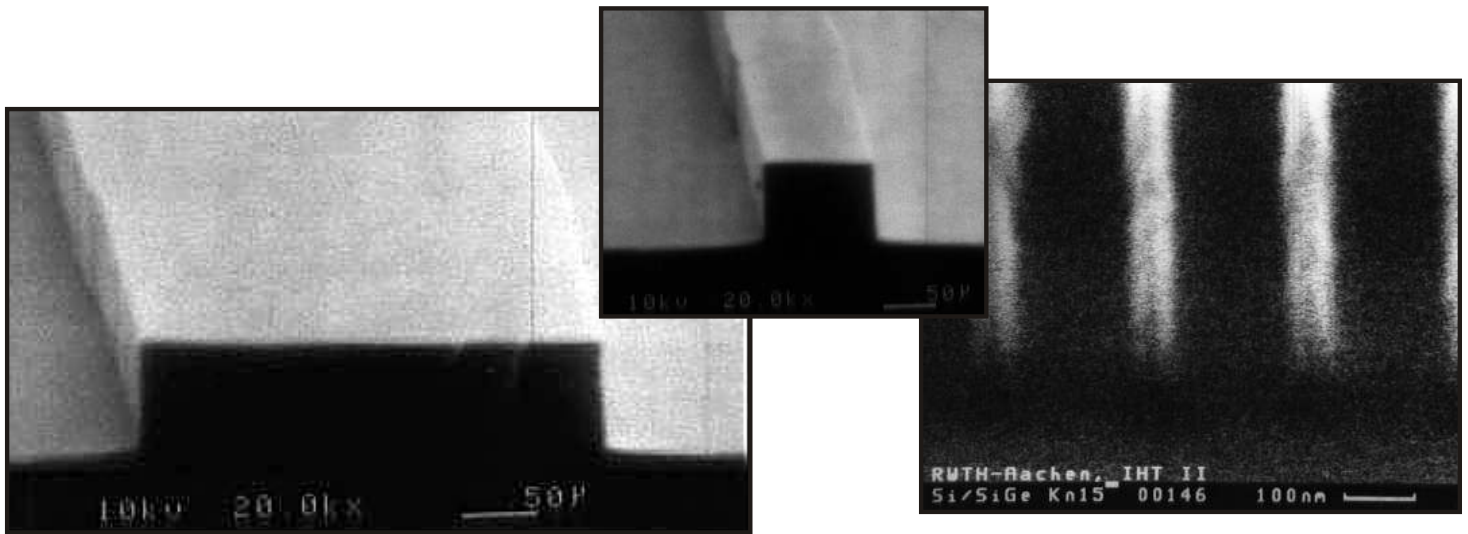


Plasmalab Data

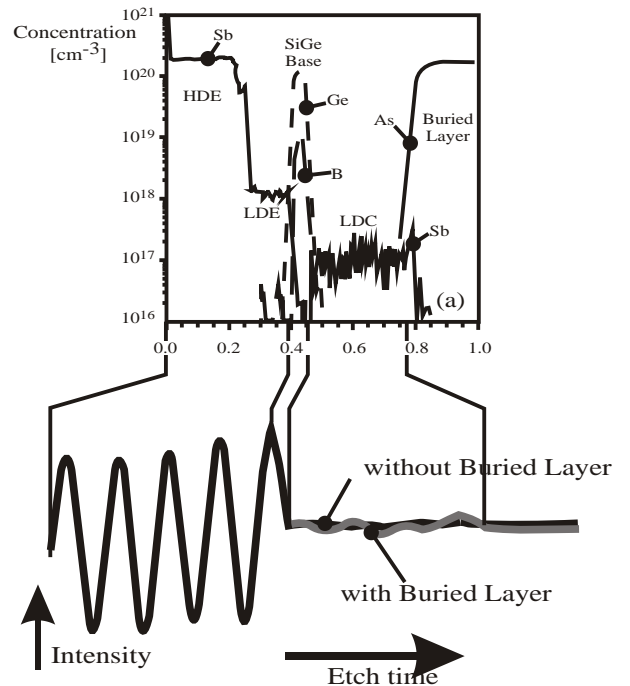
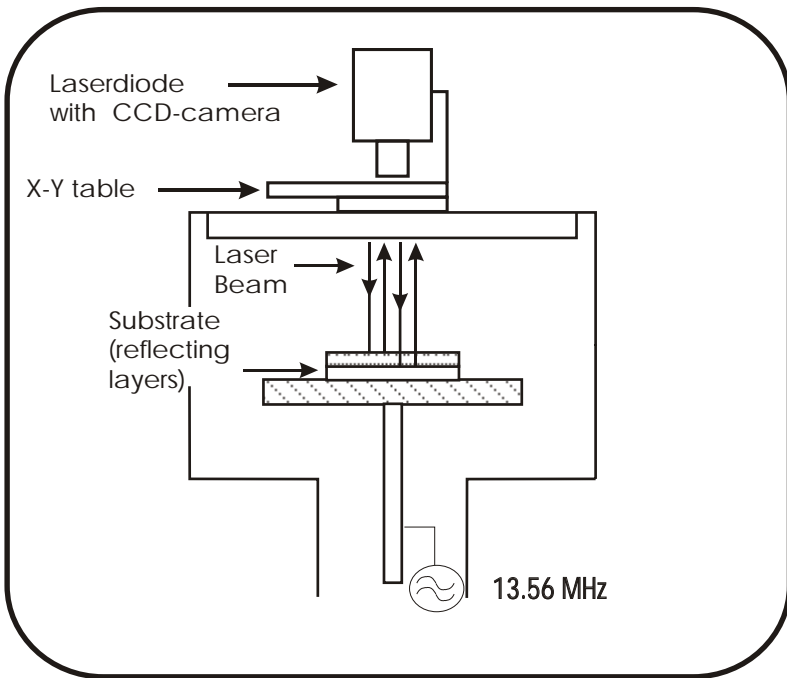
Si / SiGe / Si Heterostructure RIE using Laser Interferometry



Courtesy of the Ruhr University Bochum
 Lehrstuhl für Elektronische Bauelemente
 (left SEM's and laser signal)
 Anisotropic F Etching into a
 Si / SiGe / Si Heterostructure
 Rate ca 100 nm / min

- Plasmalab System 100*
- Plasmalab System 133*
- Plasmalab 80 Plus*

Courtesy of the RWTH Aachen
 Institut für Halbleitertechnik II
 Rate 110 nm/ min
 Trilevel Resist Mask
 Anisotropic, residue free etch
 smooth walls
 aspect ratio: 5 - 10



RIE System with laser interferometer through top electrode and the laser signal intensity versus time